

80V N-CHANNEL POWER MOSFET

DESCRIPTION:



The ALPB059N08A is an 97A, 80V N-Channel Power MOSFET and it has High Speed Power Switching.

FEATURES:

- $R_{DS(ON)} = 4.9m\Omega$ @ $V_{GS} = 10V$, I_D (Silicon Limited) = 97A, $V_{DS} = 80V$
- High Speed Power Switching
- Enhanced Body diode dv/dt capability
- Enhanced Avalanche Ruggedness
- RoHS compliant & halogen-free.
- Suffix "-H" indicated Halogen Free part, ex. ALPB059N08A-H

APPLICATIONS:

- Synchronous Rectification in SMPS.
- Hard Switching and High-Speed Circuit.
- DC/DC in Telecoms and Industrial.

MECHANICAL CHARACTERISTICS

- Epoxy: UL94-V0 rated flame retardant.
- Case: Molded plastic, TO-263
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position: Any.

MAXIMUM RATINGS

MAXIMUM RATINGS @ $T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise specified				
PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current (Silicon Limited)	@ $T_C=25^{\circ}\text{C}$	I_D	97	A
	@ $T_C=100^{\circ}\text{C}$		69	
Pulsed Drain Current		I_{DM}	280	A
Single pulse avalanche energy	$L=0.1\text{mH}$, @ $T_C=25^{\circ}\text{C}$	E_{AS}	45	mJ
Power Dissipation	@ $T_C=25^{\circ}\text{C}$	P_D	107	W
Operating Junction Temperature Range		T_J	-55 to +175	$^{\circ}\text{C}$
Storage Temperature Range		T_{STG}	-55 to +175	$^{\circ}\text{C}$
Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied. 2. Repetitive rating: pulse width limited by maximum junction temperature. 3. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.				

THERMAL CHARACTERISTICS @ $T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

PARAMETER	SYMBOL	RATINGS	UNIT
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	60	$^{\circ}\text{C/W}$
Thermal Resistance Junction to Case	$R_{\theta JC}$	1.4	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS @ TA = 25 °C unless otherwise specified

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP.	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	$V_{(BR)DSS}$	80			V
Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 80V, T_j = 25^\circ C$	I_{DSS}			1.0	μA
	$V_{GS} = 0V, V_{DS} = 80V, T_j = 100^\circ C$				100	
Gate-source leakage current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I_{GSS}			± 100	nA
ON CHARACTERISTICS						
Gate-Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	$V_{GS(TH)}$	2.0	3.0	4.0	V
Drain-to-Source On-Resistance	$V_{GS} = 10V, I_D = 20A$	$R_{DS(ON)}$		4.9	5.6	m Ω
Transconductance	$V_{DS} = 5V, I_D = 20A$	g_{fs}		50		S
Gate Resistance	$V_{GS} = 0V, V_{DS} \text{ Open}, f = 1MHz$	R_G		1.1		Ω

SWITCHING PARAMETERS						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP.	MAX	UNIT
Input Capacitance	$V_{GS} = 0V, V_{DS} = 40V, f = 1MHz$	C_{iss}		2449		pF
Output Capacitance		C_{oss}		502		
Reverse Transfer Capacitance		C_{rss}		19.0		
Total Gate Charge	$V_{DD} = 40V, I_D = 20A, V_{GS} = 10V$	Q_g		42		nC
Gate to Source Charge		Q_{gs}		8		
Gate to Drain Charge		Q_{gd}		12		
Turn-On Delay Time	$V_{DD} = 40V, I_D = 20A, V_{GS} = 10V, R_G = 10\Omega$	$t_{d(on)}$		11		nS
Rise time		t_r		7		
Turn-Off Delay Time		$t_{d(off)}$		34		
Fall time		t_f		9		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP.	MAX	UNIT
Drain forward voltage	$V_{GS} = 0V, I_F = 20A$	V_{SD}		0.9	1.2	V
Reverse recovery time	$V_R = 40V, I_F = 20A, di_F/dt = 400A/\mu s$	t_{rr}		35		ns
Reverse recovery charge		Q_{rr}		122		nC

TYPICAL DEVICE RATING AND CHARACTERISTICS CURVES ($T_A = 25^\circ\text{C}$ unless otherwise noted)

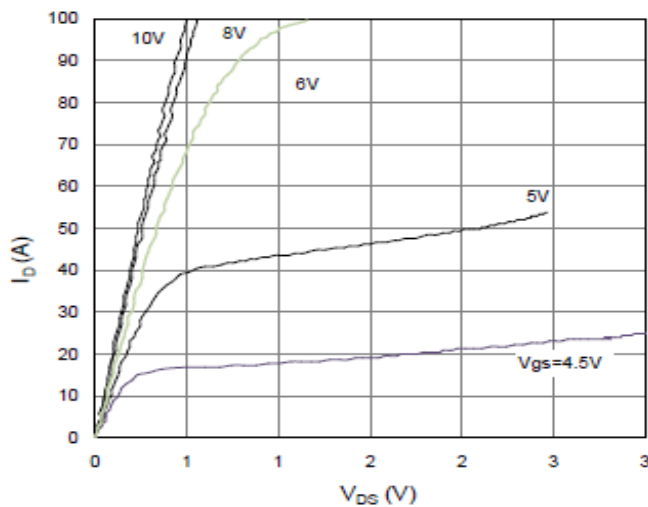


Fig.1 TYPICAL OUTPUT CHARACTERISTICS

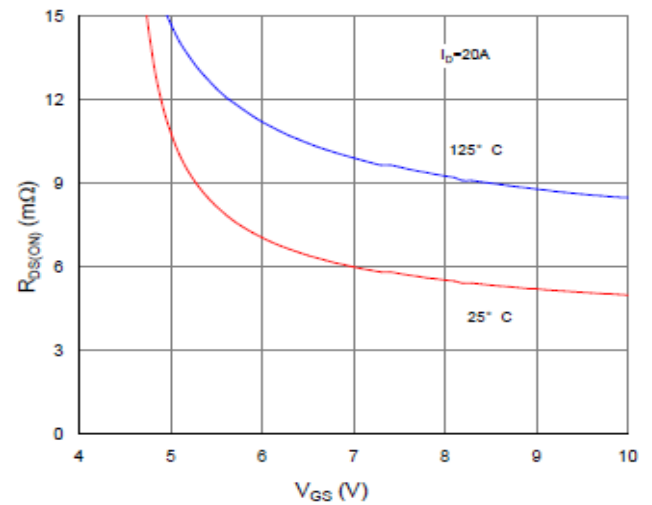


Fig.2 ON-RESISTANCE VS. GATE-SOURCE VOLTAGE

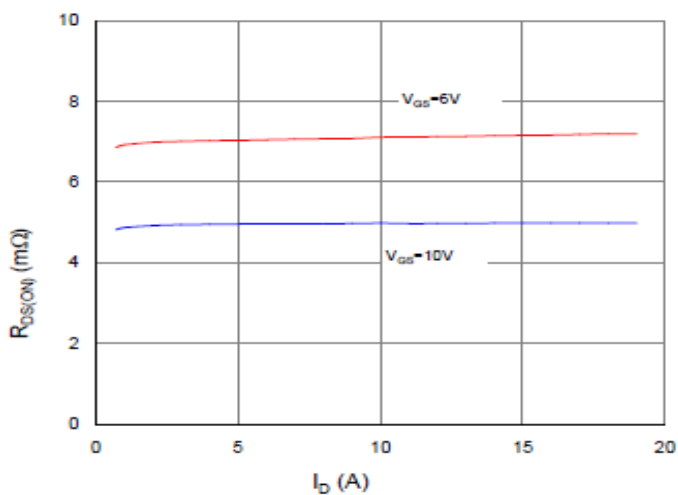


Fig.3 ON-RESISTANCE VS. DRAIN CURRENT AND GATE VOLTAGE

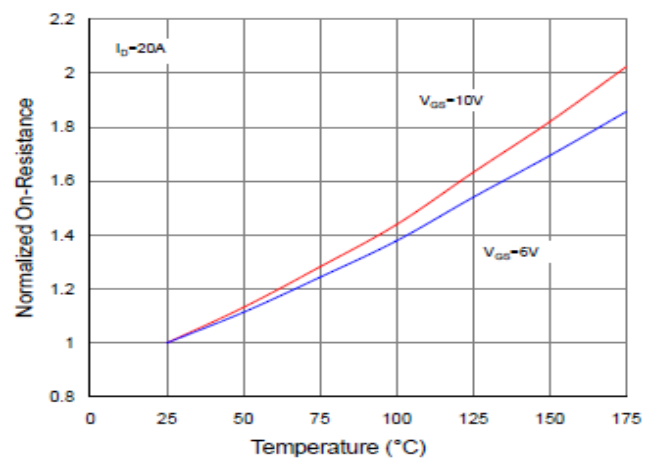


Fig.4 NORMALIZED ON-RESISTANCE VS. JUNCTION TEMPERATURE

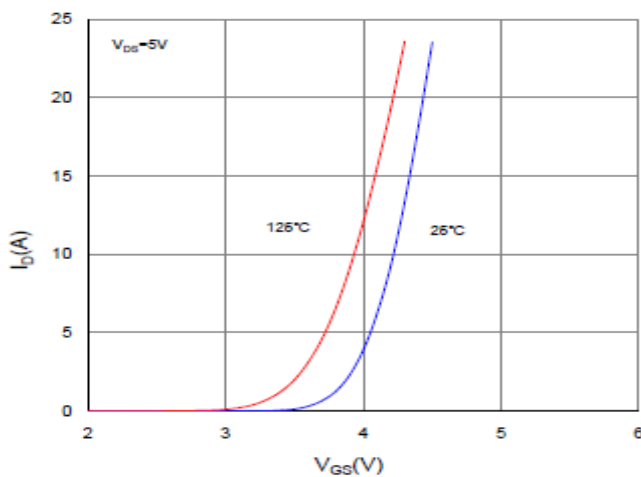


Fig.5 TYPICAL TRANSFER CHARACTERISTICS

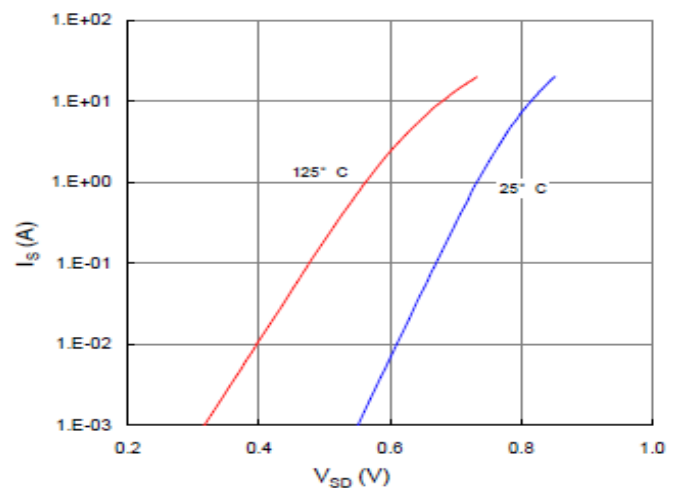


Fig.6 TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

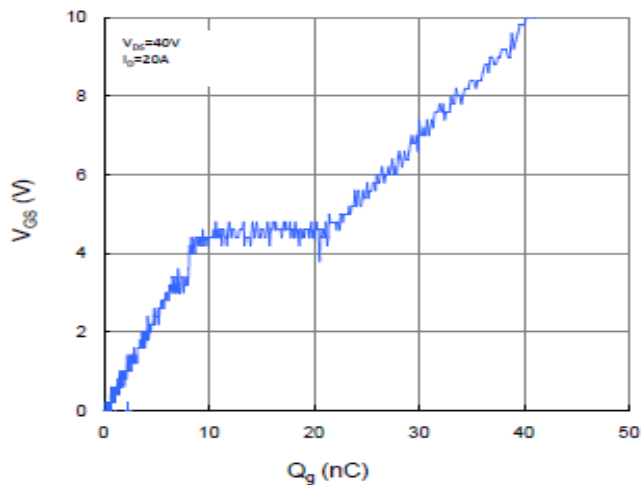


Fig.7 TYPICAL GATE-CHARGE VS. GATE-TO-SOURCE VOLTAGE

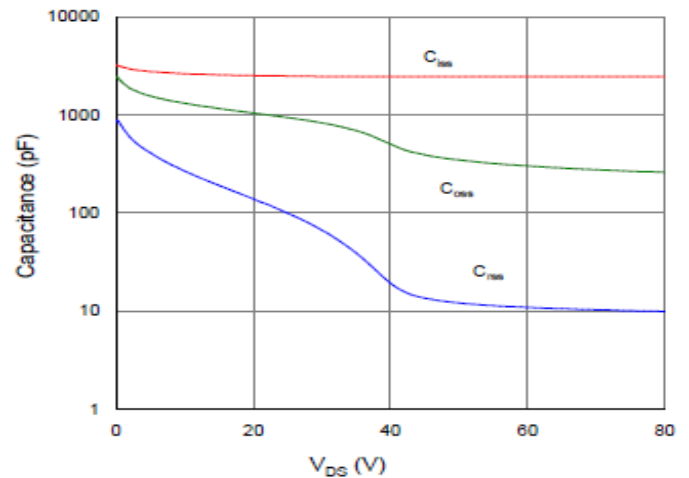


Fig.8 TYPICAL CAPACITANCE VS. DRAIN-TO-SOURCE VOLTAGE

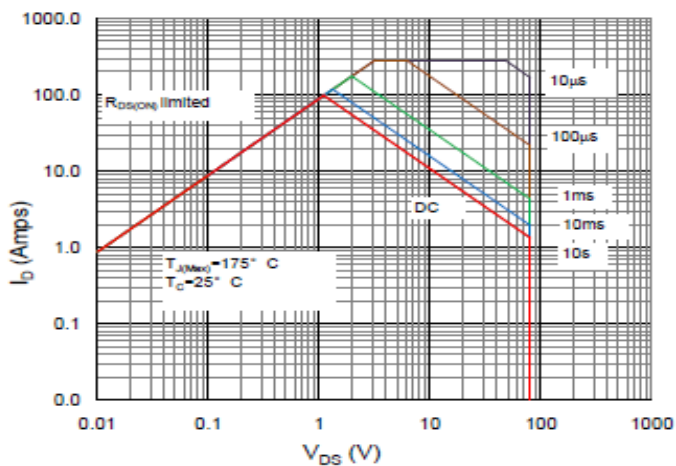


Fig.9 MAXIMUM SAFE OPERATING AREA

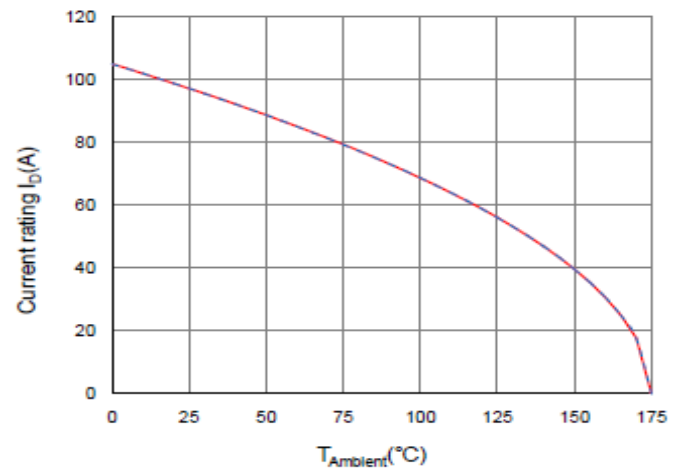


Fig.10 MAXIMUM DRAIN CURRENT VS. CASE TEMPERATURE

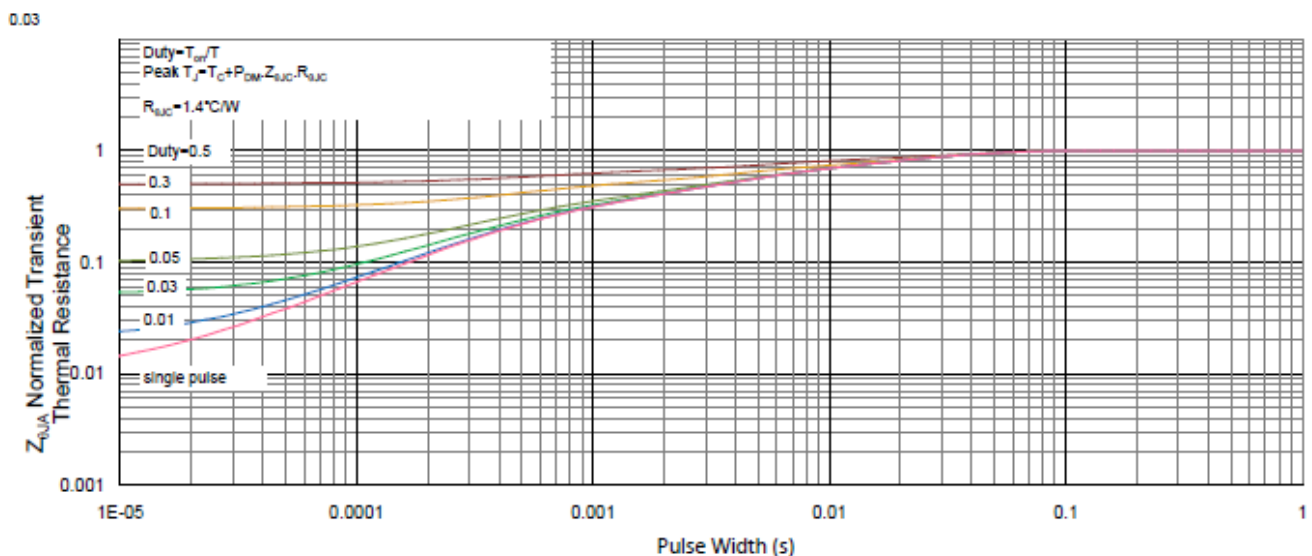
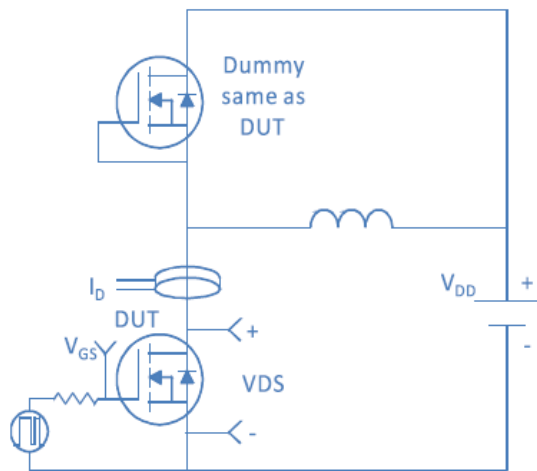
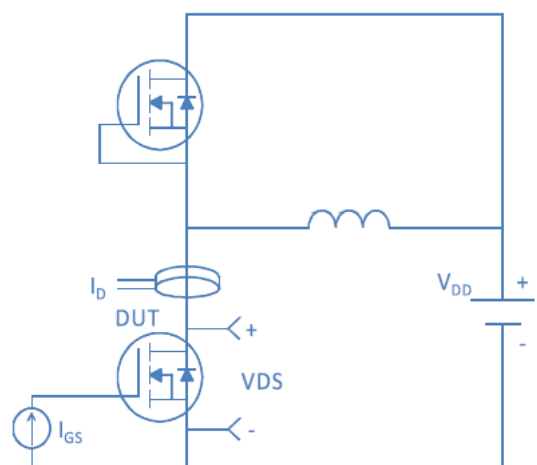
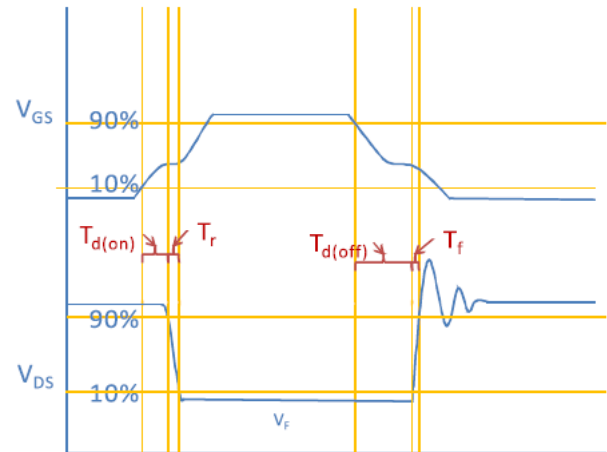


Fig.11 Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

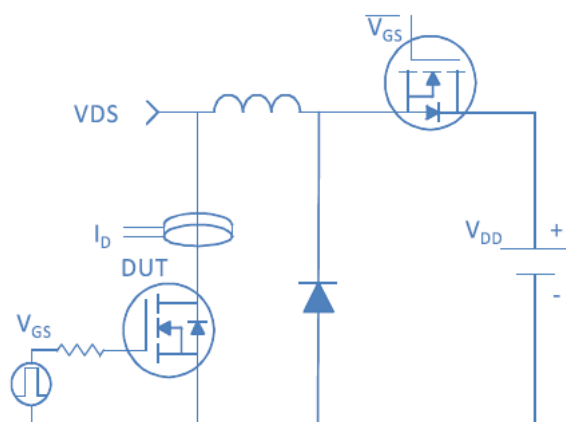
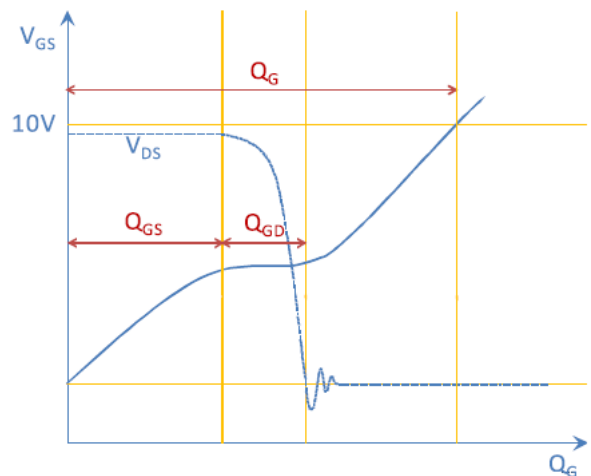
TEST RESULTS CURVES ($T_A = 25^\circ\text{C}$ unless otherwise noted)



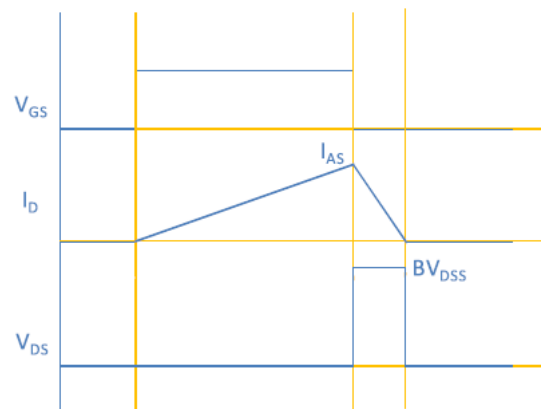
INDUCTIVE SWITCHING TEST

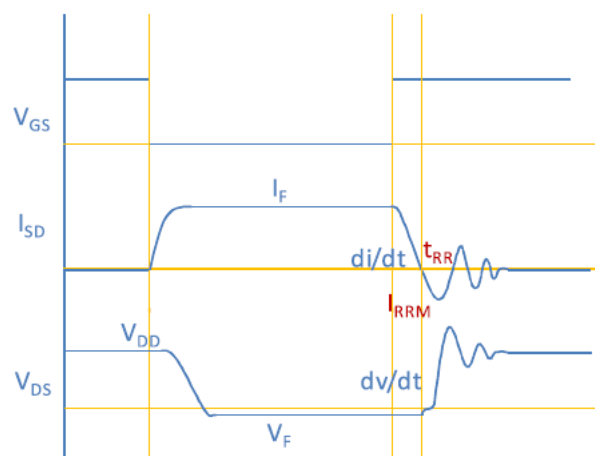
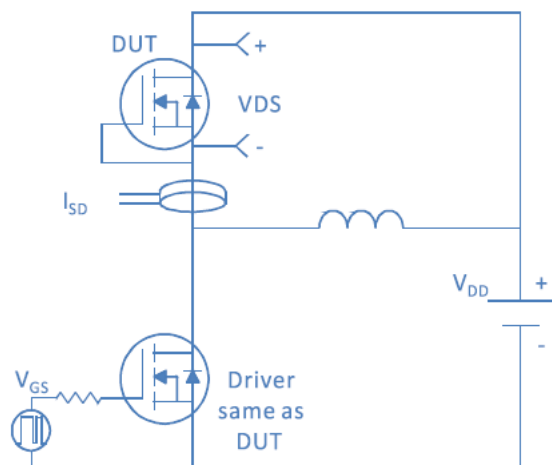


GATE CHARGE TEST



UCLAMPED INDUCTIVE SWITCHING (UIS) TEST

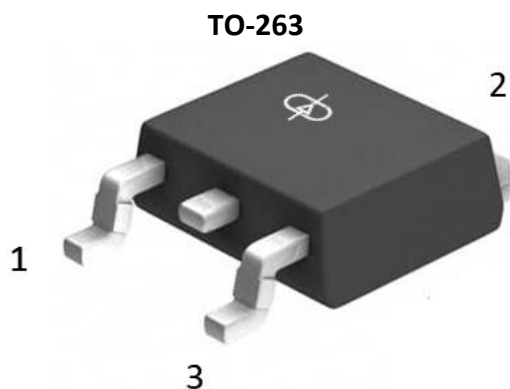




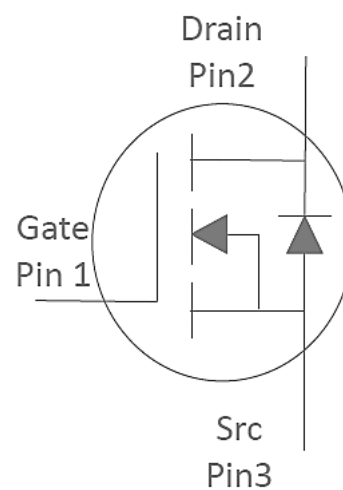
DIODE RECOVERY TEST

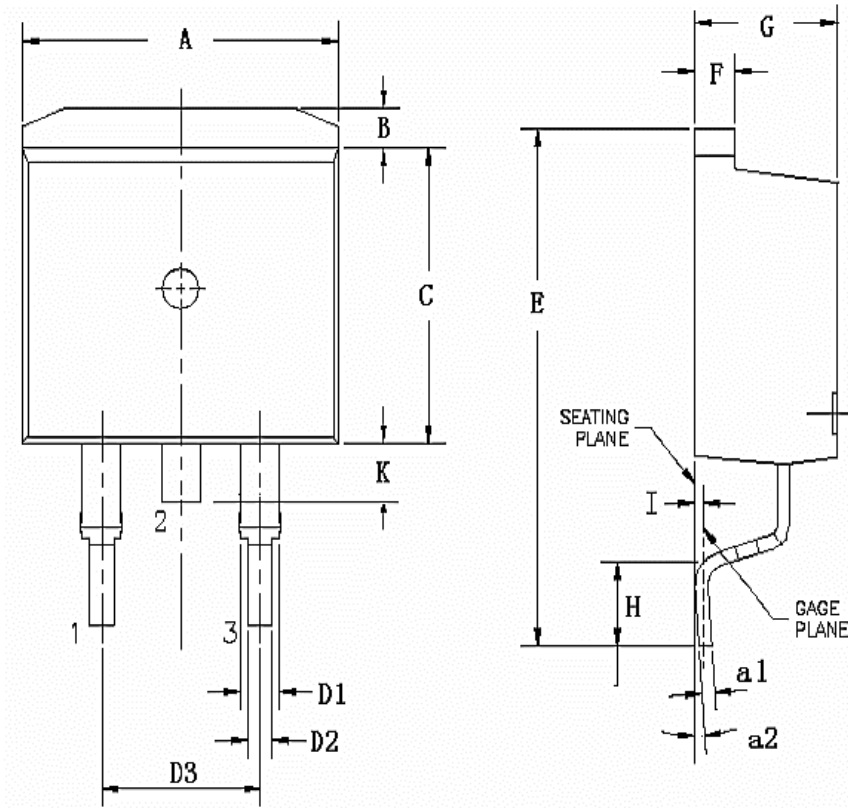
PINNING INFORMATION

SIMPLIFIED OUTLINE



SYMBOL



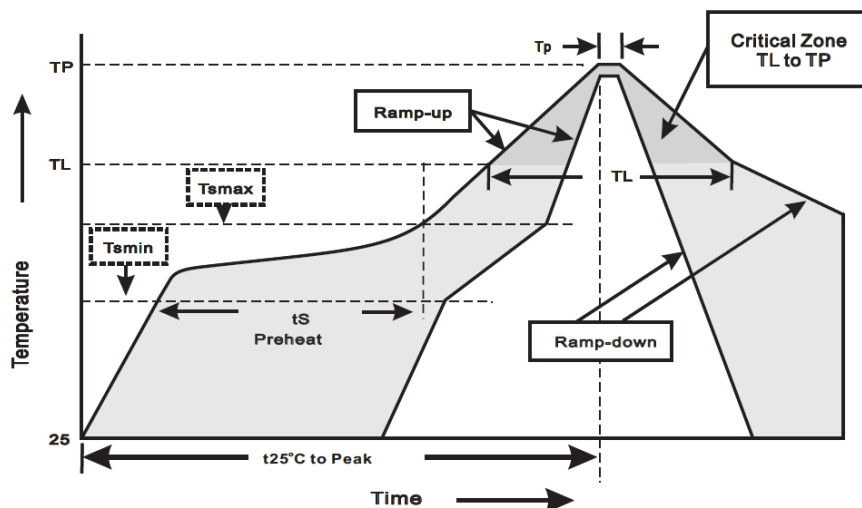
PACKAGE INFORMATION
TO-263


OUTLINE DIMENSIONS						
SYMBOL	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	9.66	9.97	10.28	0.380	0.393	0.405
B	1.02	1.17	1.32	0.040	0.046	0.052
C	8.59	9.00	9.40	0.338	0.354	0.370
D1	1.14	1.27	1.40	0.045	0.050	0.055
D2	0.70	0.83	0.95	0.028	0.033	0.037
D3	-	5.08	-	-	0.200	-
E	15.09	15.24	15.39	0.594	0.600	0.606
F	1.15	1.28	1.40	0.045	0.050	0.055
G	4.30	4.50	4.70	0.169	0.177	0.185
H	2.29	2.54	2.79	0.090	0.100	0.110
I		0.25		0.000	0.010	0.000
K	1.30	1.45	1.60	0.051	0.057	0.063
a1	0.45	0.55	0.65	0.018	0.022	0.026
a2	0°	-	8°	0°	-	8°

SOLDERING PARAMETERS

SUGGESTED THERMAL PROFILES FOR SOLDERING PROCESSES

1. Storage environment: Temperature=5 °C~40 °C Humidity=55% ±25%
2. Reflow soldering of surface-mount devices



3. Reflow soldering

PROFILE FEATURE	SOLDERING CONDITION
Average ramp-up rate (T_L to T_P)	<3 °C/sec
Preheat	
- Temperature Min (T_{smin})	150 °C
- Temperature Max (T_{smax})	200 °C
- Time (min to max) (t_s)	60 ~ 120 sec
T_{smax} to T_L	
- Ramp-upRate	<3 °C/sec
Time maintained above:	
- Temperature (T_L)	217 °C
- Time(t_L)	60 ~ 260 sec
Peak Temperature (T_P)	255 °C-0/+5 °C
Time within 5 °C of actual Peak Temperature(t_P)	10 ~ 30 sec
Ramp-down Rate	<3 °C/sec
Time 25 °C to Peak Temperature	<6 minutes



beyond boundaries...

ALPB059N08A

TO-263

CUSTOMER NOTE:

DISCLAIMER

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2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).



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